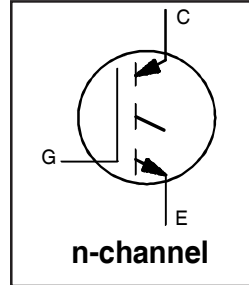


IRG4BC20WPbF

INSULATED GATE BIPOLAR TRANSISTOR

Features

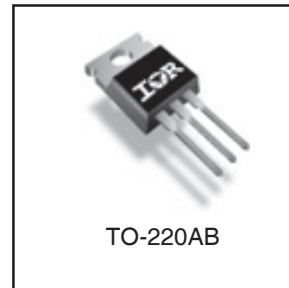
- Designed expressly for Switch-Mode Power Supply and PFC (power factor correction) applications
- Industry-benchmark switching losses improve efficiency of all power supply topologies
- 50% reduction of Eoff parameter
- Low IGBT conduction losses
- Latest-generation IGBT design and construction offers tighter parameters distribution, exceptional reliability
- Lead-Free



$V_{CES} = 600V$
$V_{CE(on)} \text{ typ.} = 2.16V$
@ $V_{GE} = 15V, I_C = 6.5A$

Benefits

- Lower switching losses allow more cost-effective operation than power MOSFETs up to 150 kHz ("hard switched" mode)
- Of particular benefit to single-ended converters and boost PFC topologies 150W and higher
- Low conduction losses and minimal minority-carrier recombination make these an excellent option for resonant mode switching as well (up to >>300 kHz)



Absolute Maximum Ratings

	Parameter	Max.	Units
V_{CES}	Collector-to-Emitter Breakdown Voltage	600	V
$I_C @ T_C = 25^\circ C$	Continuous Collector Current	13	A
$I_C @ T_C = 100^\circ C$	Continuous Collector Current	6.5	
I_{CM}	Pulsed Collector Current ①	52	
I_{LM}	Clamped Inductive Load Current ②	52	
V_{GE}	Gate-to-Emitter Voltage	± 20	V
E_{ARV}	Reverse Voltage Avalanche Energy ③	200	mJ
$P_D @ T_C = 25^\circ C$	Maximum Power Dissipation	60	W
$P_D @ T_C = 100^\circ C$	Maximum Power Dissipation	24	
T_J	Operating Junction and Storage Temperature Range	-55 to + 150	°C
T_{STG}	Soldering Temperature, for 10 seconds	300 (0.063 in. (1.6mm) from case)	
	Mounting torque, 6-32 or M3 screw.	10 lbf•in (1.1N•m)	

Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	---	2.1	°C/W
$R_{\theta CS}$	Case-to-Sink, Flat, Greased Surface	0.5	---	
$R_{\theta JA}$	Junction-to-Ambient, typical socket mount	---	80	
Wt	Weight	2.0 (0.07)	---	g (oz)

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Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)CES}$	Collector-to-Emitter Breakdown Voltage	600	—	—	V	$V_{GE} = 0V, I_C = 250\mu A$
$V_{(BR)ECS}$	Emitter-to-Collector Breakdown Voltage ④	18	—	—	V	$V_{GE} = 0V, I_C = 1.0A$
$\Delta V_{(BR)CES}/\Delta T_J$	Temperature Coeff. of Breakdown Voltage	—	0.48	—	V/°C	$V_{GE} = 0V, I_C = 1.0mA$
$V_{CE(ON)}$	Collector-to-Emitter Saturation Voltage	—	2.16	2.6	V	$I_C = 6.5A, V_{GE} = 15V$ See Fig.2, 5
		—	2.55	—		
		—	2.05	—		
$V_{GE(th)}$	Gate Threshold Voltage	3.0	—	6.0		$I_C = 6.5A, T_J = 150^\circ\text{C}$ $V_{CE} = V_{GE}, I_C = 250\mu A$
$\Delta V_{GE(th)}/\Delta T_J$	Temperature Coeff. of Threshold Voltage	—	-8.8	—	mV/°C	$V_{CE} = V_{GE}, I_C = 250\mu A$
g_{fe}	Forward Transconductance ⑤	5.5	8.3	—	S	$V_{CE} = 100V, I_C = 6.5A$
I_{CES}	Zero Gate Voltage Collector Current	—	—	250	μA	$V_{GE} = 0V, V_{CE} = 600V$ $V_{GE} = 0V, V_{CE} = 10V, T_J = 25^\circ\text{C}$ $V_{GE} = 0V, V_{CE} = 600V, T_J = 150^\circ\text{C}$
		—	—	2.0		
		—	—	1000		
I_{GES}	Gate-to-Emitter Leakage Current	—	—	± 100	nA	$V_{GE} = \pm 20V$

Switching Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
Q_g	Total Gate Charge (turn-on)	—	26	38	nC	$I_C = 6.5A$ $V_{CC} = 400V$ See Fig.8 $V_{GE} = 15V$
Q_{ge}	Gate - Emitter Charge (turn-on)	—	3.7	5.5		
Q_{gc}	Gate - Collector Charge (turn-on)	—	10	15		
$t_{d(on)}$	Turn-On Delay Time	—	22	—	ns	$T_J = 25^\circ\text{C}$ $I_C = 6.5A, V_{CC} = 480V$ $V_{GE} = 15V, R_G = 50\Omega$ Energy losses include "tail" See Fig. 9, 10, 14
t_r	Rise Time	—	14	—		
$t_{d(off)}$	Turn-Off Delay Time	—	110	160		
t_f	Fall Time	—	64	96		
E_{on}	Turn-On Switching Loss	—	0.06	—	mJ	See Fig. 9, 10, 14
E_{off}	Turn-Off Switching Loss	—	0.08	—		
E_{ts}	Total Switching Loss	—	0.14	0.2	ns	$T_J = 150^\circ\text{C}$, $I_C = 6.5A, V_{CC} = 480V$ $V_{GE} = 15V, R_G = 50\Omega$ Energy losses include "tail" See Fig. 10, 11, 14
$t_{d(on)}$	Turn-On Delay Time	—	21	—		
t_r	Rise Time	—	15	—		
$t_{d(off)}$	Turn-Off Delay Time	—	150	—		
t_f	Fall Time	—	150	—		
E_{ts}	Total Switching Loss	—	0.34	—	mJ	See Fig. 10, 11, 14
L_E	Internal Emitter Inductance	—	7.5	—	nH	Measured 5mm from package
C_{ies}	Input Capacitance	—	490	—	pF	$V_{GE} = 0V$ $V_{CC} = 30V$ See Fig. 7 $f = 1.0MHz$
C_{oes}	Output Capacitance	—	38	—		
C_{res}	Reverse Transfer Capacitance	—	8.8	—		

Notes:

- ① Repetitive rating; $V_{GE} = 20V$, pulse width limited by max. junction temperature. (See fig. 13b)
- ② $V_{CC} = 80\%(V_{CES}), V_{GE} = 20V, L = 10\mu H, R_G = 50\Omega$, (See fig. 13a)
- ③ Repetitive rating; pulse width limited by maximum junction temperature.
- ④ Pulse width $\leq 80\mu s$; duty factor $\leq 0.1\%$.
- ⑤ Pulse width $5.0\mu s$, single shot.

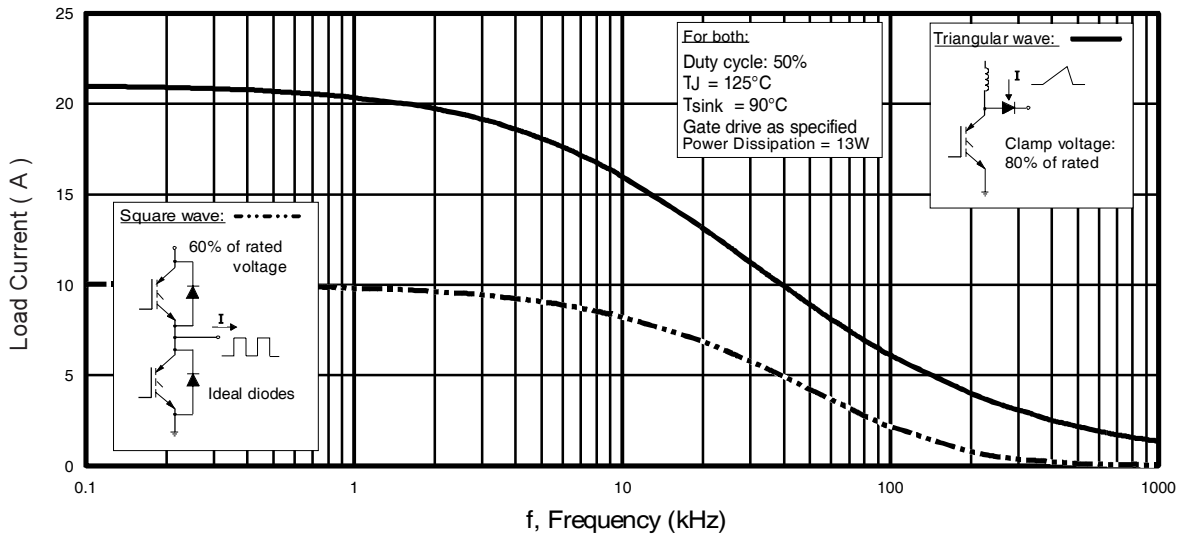


Fig. 1 - Typical Load Current vs. Frequency
(Load Current = I_{RMS} of fundamental)

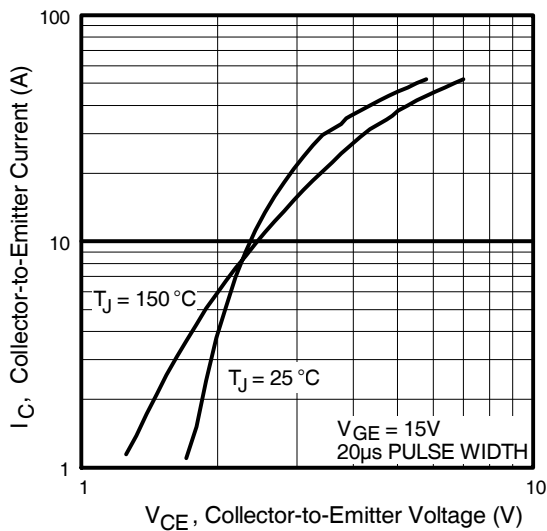


Fig. 2 - Typical Output Characteristics
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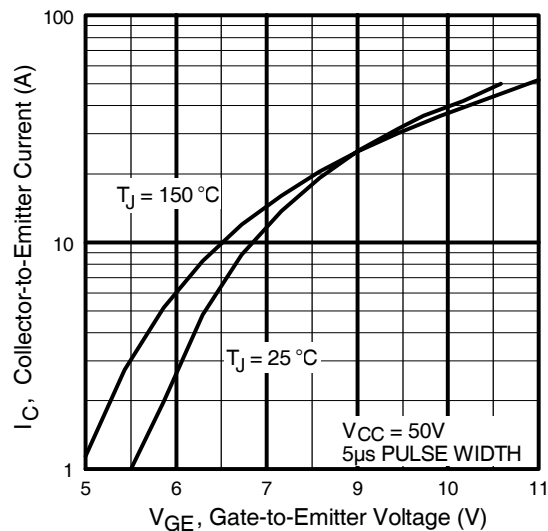


Fig. 3 - Typical Transfer Characteristics

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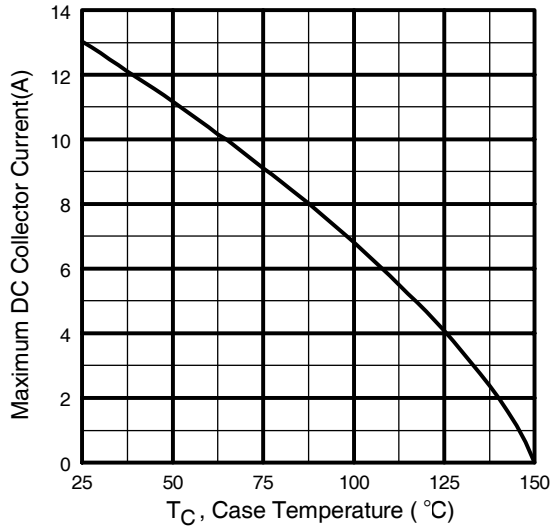


Fig. 4 - Maximum Collector Current vs. Case Temperature

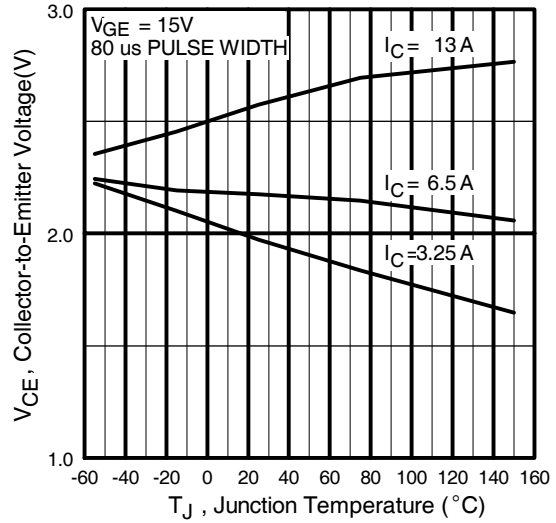


Fig. 5 - Typical Collector-to-Emitter Voltage vs. Junction Temperature

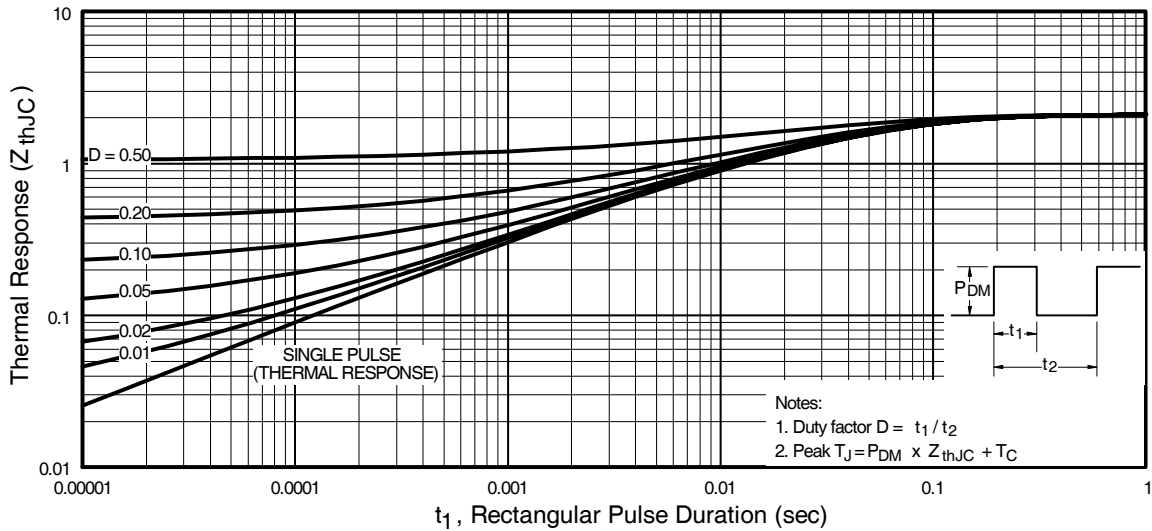


Fig. 6 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

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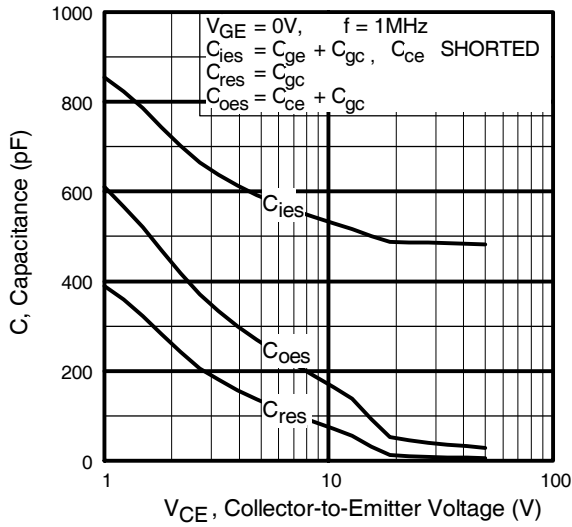


Fig. 7 - Typical Capacitance vs. Collector-to-Emitter Voltage

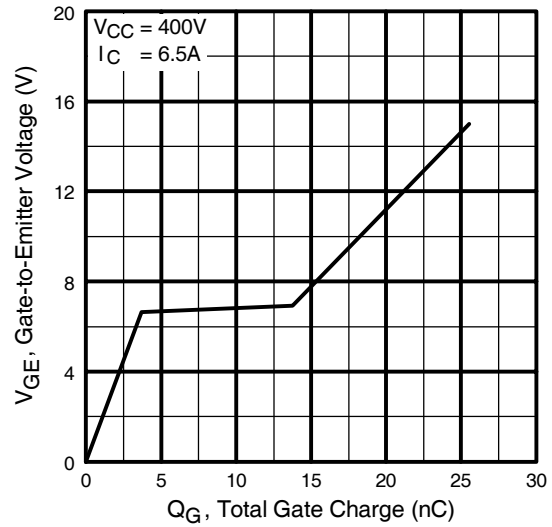


Fig. 8 - Typical Gate Charge vs. Gate-to-Emitter Voltage

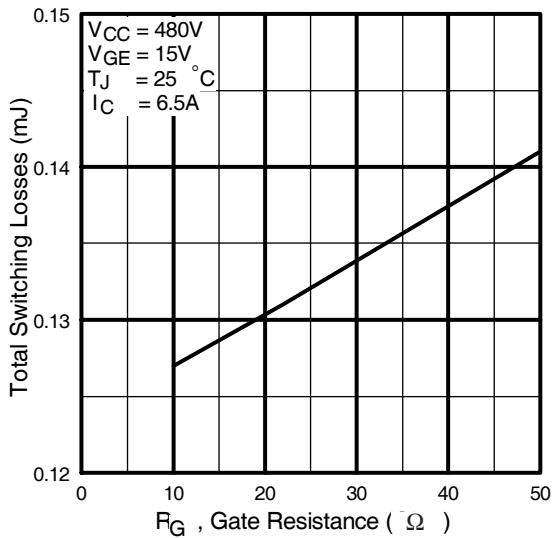


Fig. 9 - Typical Switching Losses vs. Gate Resistance

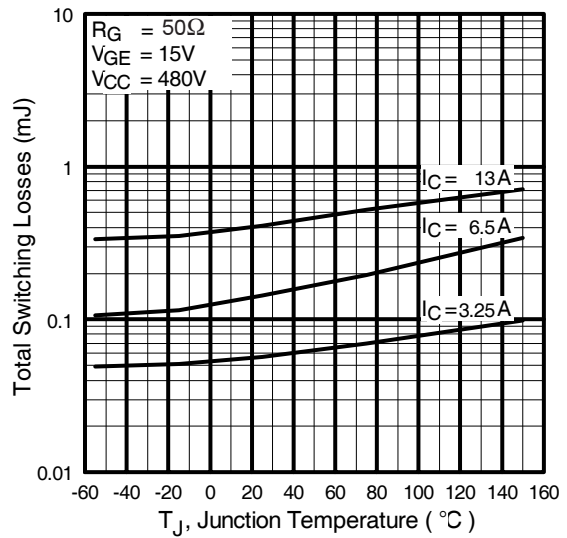


Fig. 10 - Typical Switching Losses vs. Junction Temperature

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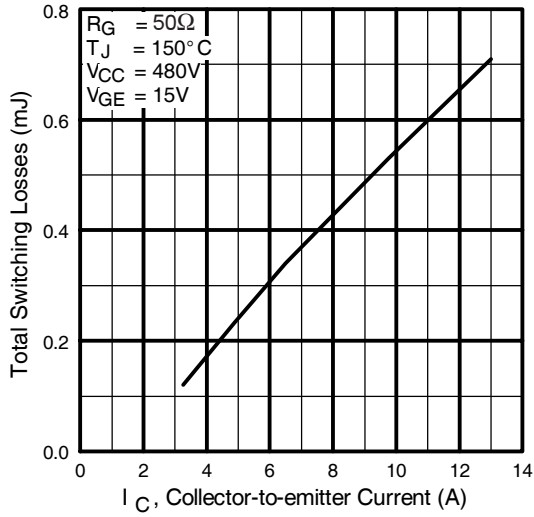


Fig. 11 - Typical Switching Losses vs. Collector-to-Emitter Current

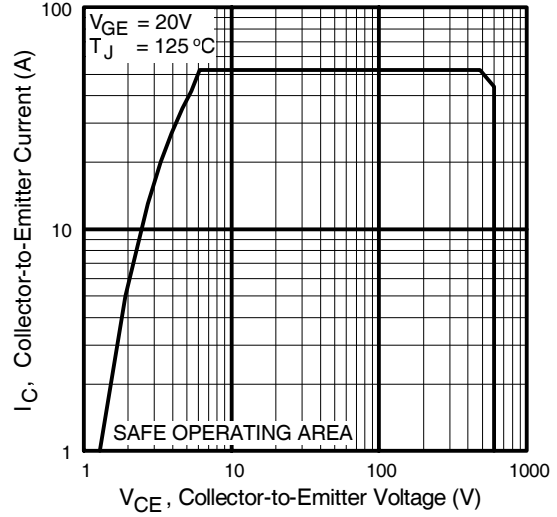
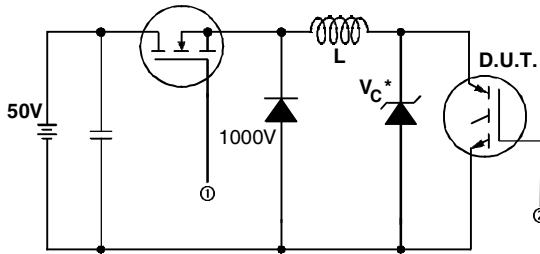


Fig. 12 - Turn-Off SOA

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* Driver same type as D.U.T.; $V_c = 80\%$ of $V_{ce(max)}$
 * Note: Due to the 50V power supply, pulse width and inductor will increase to obtain rated I_d .

Fig. 13a - Clamped Inductive Load Test Circuit

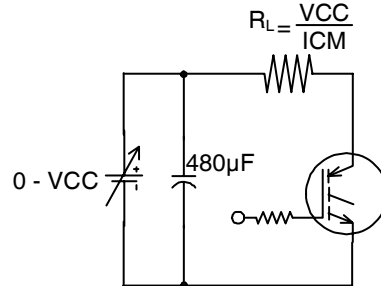


Fig. 13b - Pulsed Collector Current Test Circuit

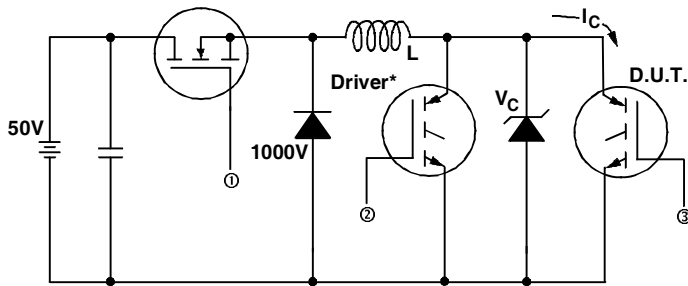


Fig. 14a - Switching Loss Test Circuit

* Driver same type as D.U.T., $V_C = 480V$

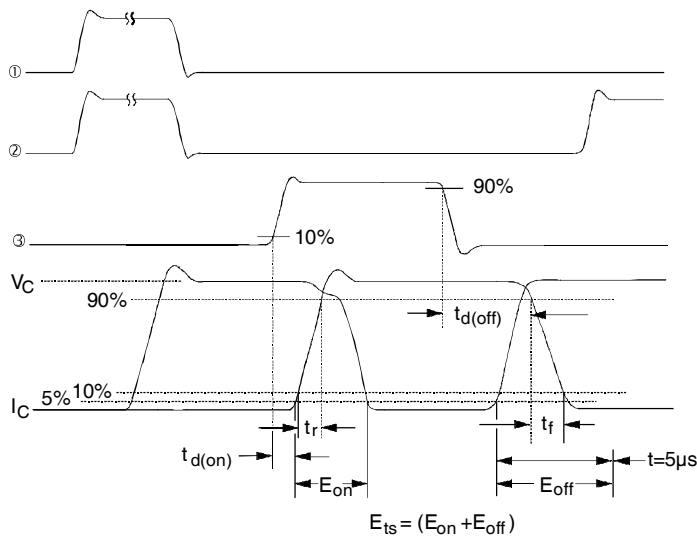
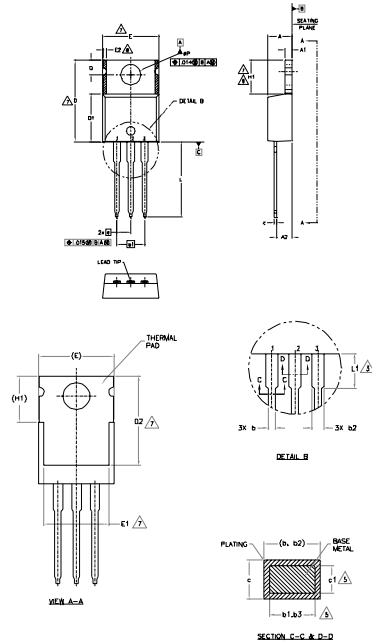


Fig. 14b - Switching Loss Waveforms

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TO-220AB Package Outline (Dimensions are shown in millimeters (inches))



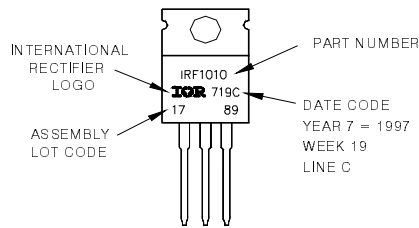
- NOTES:
- 1 - DIMENSIONING AND TOLERANCING AS PER ASME Y14.5 M- 1994
 - 2 - DIMENSIONS ARE SHOWN IN INCHES (MILLIMETERS)
 - 3 - LEAD DIMENSION AND HIGH UNCONTROLLED IN L1
 - 4 - DIMENSION D, D1 & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
 - 5 - DIMENSION D1, b2 & c1 APPLY TO BASE METAL ONLY.
 - 6 - CONTROLLING DIMENSION - INCHES.
 - 7 - THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS E, H1, D2 & E1
 - 8 - DIMENSION E2 x H1 DEFINE A ZONE WHERE STAMPING AND SOLDERING IRREGULARITIES ARE ALLOWED.
 - 9 - OUTLINE CONFORMS TO JEDEC TO-220 EXCEPT A2 (max.) AND D2 (min.) WHERE DIMENSIONS ARE DERIVED FROM THE ACTUAL PACKAGE OUTLINE.

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	3.56	4.83	.140	.190	
A1	0.51	1.40	.020	.055	
A2	2.03	2.92	.080	.115	
b	0.38	1.01	.015	.040	
b1	0.38	0.97	.015	.038	5
b2	1.14	1.78	.045	.070	
b3	1.14	1.73	.045	.068	5
c	0.26	0.61	.014	.024	
c1	0.36	0.56	.014	.022	5
D	14.22	16.51	.560	.650	4
D1	8.28	9.02	.330	.355	
D2	11.68	12.86	.460	.507	7
E	9.65	10.67	.380	.420	4,7
E1	6.86	8.89	.270	.350	7
E2	-	0.76	-	.030	8
e	2.54 BSC		.100 BSC		
e1	3.08 BSC		.120 BSC		
H1	5.84	6.86	.230	.270	7,8
L	12.70	14.73	.500	.580	
L1	3.56	4.06	.140	.160	3
WP	3.54	4.08	.139	.161	
Q	2.54	3.42	.100	.135	

- LEAD ASSIGNMENTS
- 1 - GATE
 - 2 - SIGNAL
 - 3 - SOURCE
- WIRE GAUGE
- 1 - GATE
 - 2 - COLLECTOR
 - 3 - EMITTER
- DIODES
- 1 - ANODE
 - 2 - CATHODE
 - 3 - ANODE

TO-220AB Part Marking Information

EXAMPLE: THIS IS AN IRF1010
 LOT CODE 1789
 ASSEMBLED ON WW 19, 1997
 IN THE ASSEMBLY LINE 'C'
Note: "P" in assembly line position indicates "Lead-Free"



Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

Data and specifications subject to change without notice.



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[RJH60F3DPQ-A0#T0](#) [APT40GR120B2SCD10](#) [APT15GT120BRG](#) [APT20GT60BRG](#) [NGTB75N65FL2WAG](#) [NGTG15N120FL2WG](#)
[IXA30RG1200DHGLB](#) [IXA40RG1200DHGLB](#) [APT70GR65B2DU40](#) [NTE3320](#) [QP12W05S-37A](#) [IHF40N65R5SFKSA1](#) [APT70GR120J](#)
[APT35GP120JDQ2](#) [IKZA40N65RH5XKSA1](#) [IKFW75N65ES5XKSA1](#) [IKFW50N65ES5XKSA1](#) [IKFW50N65EH5XKSA1](#)
[IKFW40N65ES5XKSA1](#) [IKFW60N65ES5XKSA1](#) [IMBG120R090M1HXTMA1](#) [IMBG120R220M1HXTMA1](#) [XD15H120CX1](#)
[XD25H120CX0](#) [XP15PJS120CL1B1](#) [IGW30N60H3FKSA1](#) [STGWA8M120DF3](#) [IGW08T120FKSA1](#) [IGW75N60H3FKSA1](#)
[FGH60N60SMD_F085](#) [FGH75T65UPD](#) [STGWA15H120F2](#) [IKA10N60TXKSA1](#) [IHW20N120R5XKSA1](#) [RJH60D2DPP-M0#T2](#)
[IKP20N60TXKSA1](#) [IHW20N65R5XKSA1](#)